

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently amended) A semiconductor device comprising:
a light-transmitting substrate;
a base film having ~~a projection~~ first and second projections, the film being formed over one surface of the light-transmitting substrate;
[[an]] a first island-like semiconductor layer having a crystal structure entirely covering the first projection and extending over a pair of edges of the first projection;
a gate insulating film over the first island-like semiconductor layer; [[and]]
a gate electrode over the gate insulating film[[.]];
a second island like semiconductor layer having a first portion covering the second projection and a second portion not covering the second projection; and
a capacitor comprising the second portion.

2. (Currently Amended) A semiconductor device comprising:
a light-transmitting substrate;
a base film having ~~a projection~~ first and second projections is provided over one surface of the light-transmitting substrate;
a first thin film transistor comprising:
[[an]] a first island-like semiconductor layer comprising a channel formation region, wherein at least a part of the channel formation region is provided over the first projection, and wherein the island-like semiconductor layer entirely covers the first projection and extends over a pair of edges of the projection;
a gate insulating film over the first island-like semiconductor layer; and
a gate electrode over the gate insulating film[[.]];

a second thin film transistor comprising:

a first portion of a second island like semiconductor layer covering the second projection; and

a capacitor comprising a second portion of the second island like semiconductor layer not covering the second projection.

3. (Previously Presented) A semiconductor device according to claim 1, wherein a height of the projection is 30 to 100 nm.

4. (Previously Presented) A semiconductor device according to claim 2, wherein a height of the projection is 30 to 100 nm.

5.-10. (Canceled)

11. (Currently Amended) A semiconductor device comprising:

a light-transmitting substrate;

a base film having ~~a region~~ first and second regions of a first thickness and a ~~region~~ third region of a second thickness, over one surface of the light-transmitting substrate, wherein the second thickness is smaller than the first thickness, and wherein ~~an area of the region~~ each of the first and second regions of the first thickness is smaller than an area of the third region of the second thickness;

~~[[an]]~~ a first island-like semiconductor layer having a crystal structure over the first region of the first thickness and the third region of the second thickness,

a first gate insulating film over the first island-like semiconductor layer; and

a first gate electrode over the first gate insulating film,

wherein the first island-like semiconductor layer entirely covers the first region of the first thickness~~[.]~~.

a second island like semiconductor layer having a first portion over the second region of the first thickness and a second portion over the third region of the second thickness; and

a capacitor comprising the second portion.

12. (Currently Amended) A semiconductor device comprising:

a light-transmitting substrate;

a base film having a region first and second regions of a first thickness and a third region of a second thickness, over one surface of the light-transmitting substrate, wherein the second thickness is smaller than the first thickness, and wherein an area of the region each of the first and second regions of the first thickness is smaller than an area of the third region of the second thickness;

a first thin film transistor comprising:

a channel formation region, wherein at least a part of the channel formation region is provided over the first region of the first thickness;

source and drain regions, wherein at least a part of the source and drain regions is provided over the third region of the second thickness,

wherein the channel formation region and the source and drain regions entirely cover the region of the first thickness;

a gate insulating film over the channel formation region, and the source and drain regions; and

a gate electrode over the gate insulating film[[.]].

a second thin film transistor comprising:

a first portion of a second island like semiconductor layer over the second region of the first thickness; and

a capacitor comprising a second portion of the second island like semiconductor layer over the third region of the second thickness.

13. (Previously Presented) A semiconductor device according to claim 11, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

14. (Previously Presented) A semiconductor device according to claim 12, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

15. (Previously Presented) A semiconductor device according to claim 1, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

16. (Previously Presented) A semiconductor device according to claim 2, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

17. (Previously Presented) A semiconductor device according to claim 11, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

18. (Previously Presented) A semiconductor device according to claim 12, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

19. (Previously Presented) A semiconductor device according to claim 1, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an

electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

20. (Previously Presented) A semiconductor device according to claim 2, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

21. (Previously Presented) A semiconductor device according to claim 11, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

22. (Previously Presented) A semiconductor device according to claim 12, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.